

Electronic Supplementary Information

Self-supporting network structured MoS₂/heteroatom doped graphene as superior anode materials for sodium storage

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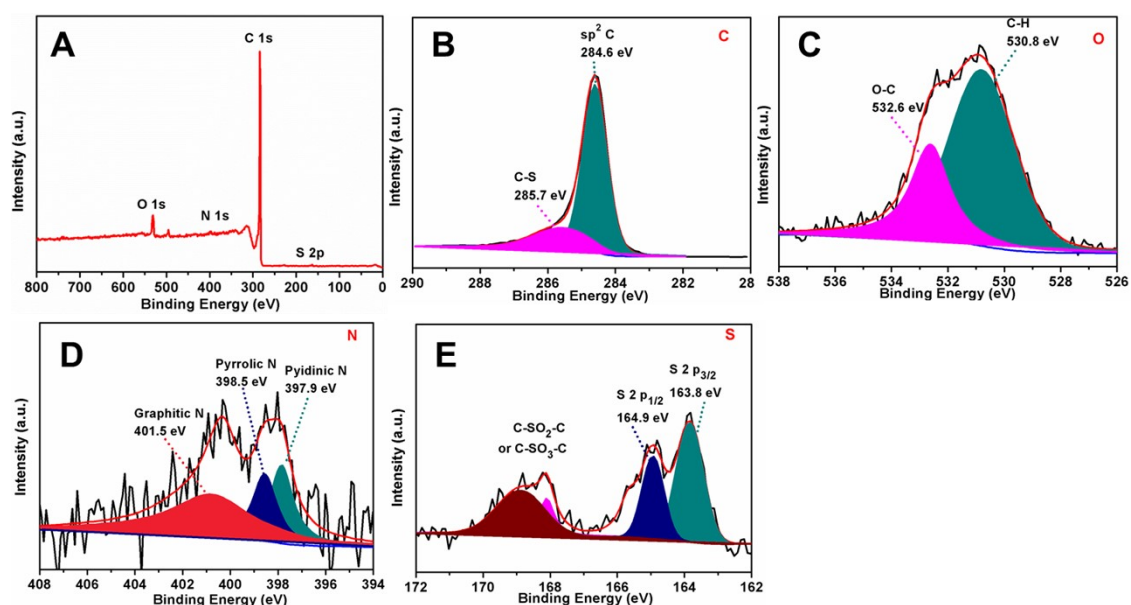


Fig. S1 XPS spectra of the N, S co-doped graphene nanosheets (A) and the corresponding high-resolution of C 1s (B), O 1s (C), N 1s (D) and S 2p (E).

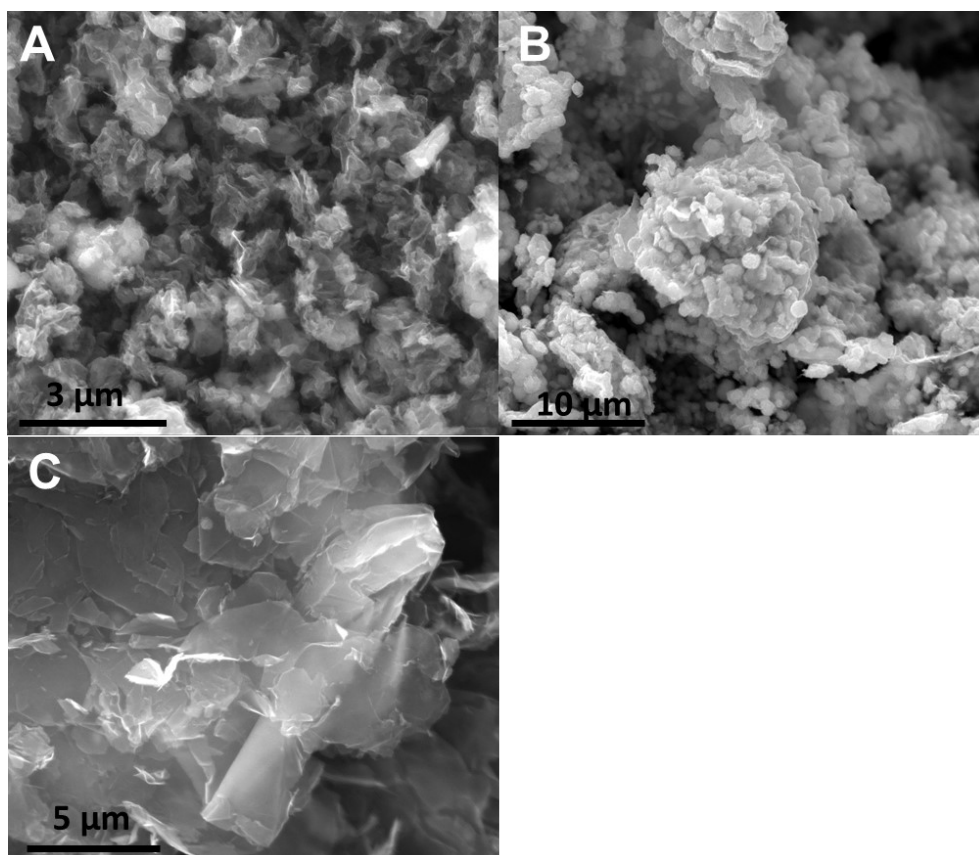


Fig. S2 SEM images of MoS₂/Gs-G (A), bulk MoS₂ (B) and bulk N, S co-doped graphene (C) samples.

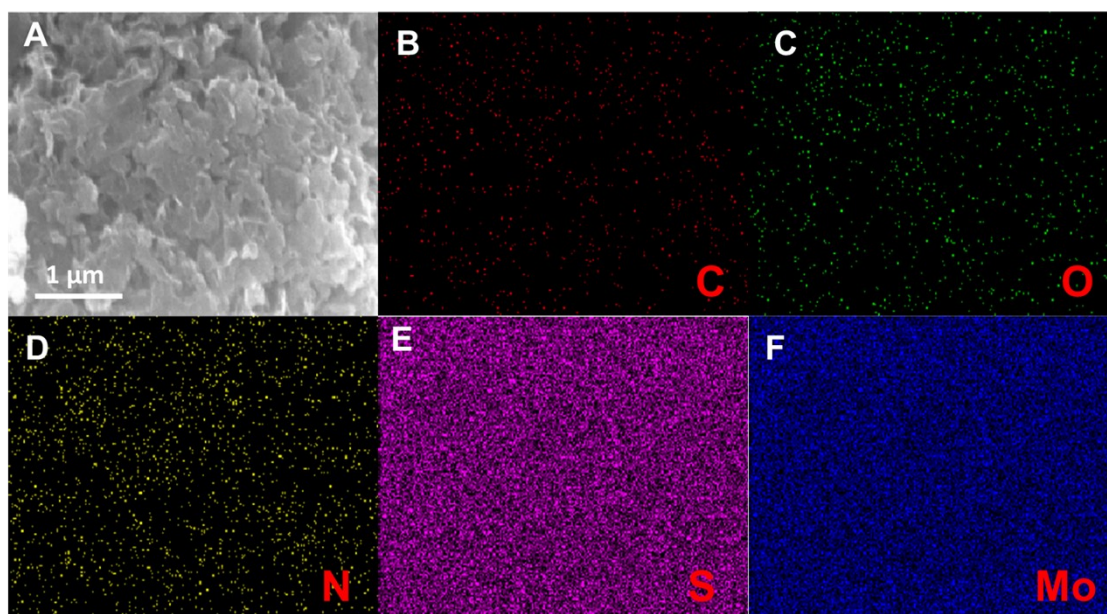


Fig. S3 SEM image of MoS₂/NSGs-G sample (A) and corresponding elemental mapping images of C (B), O (C), N (D), S (E) and Mo (F).

Table S1 The rate charge capacity of MoS₂/NSGs-G, MoS₂/Gs-G, bulk N, S co-doped graphene

and bulk1 MoS₂ at different current densities.

Samples	Specific capacity (mAh g ⁻¹)							
	0.1A g ⁻	0.2A g ⁻	0.5 A g ⁻	1 A g ⁻	2 A g ⁻	5 A g ⁻	10 A g ⁻	0.1A g ⁻
	1	1	1	1	1	1	1	1
MoS₂/NSGs-G	496.6	493.5	453.9	418.1	383.8	333.1	294.4	507.3
MoS₂/Gs-G	453.2	436.8	402.6	366.0	325.4	270.9	234.6	445.8
Bulk graphene	344.8	327.2	315.7	303.2	286.5	248.5	238.7	397.7
Bulk MoS₂	262.8	272.1	270.0	258.9	243.3	215.3	211.2	289.8

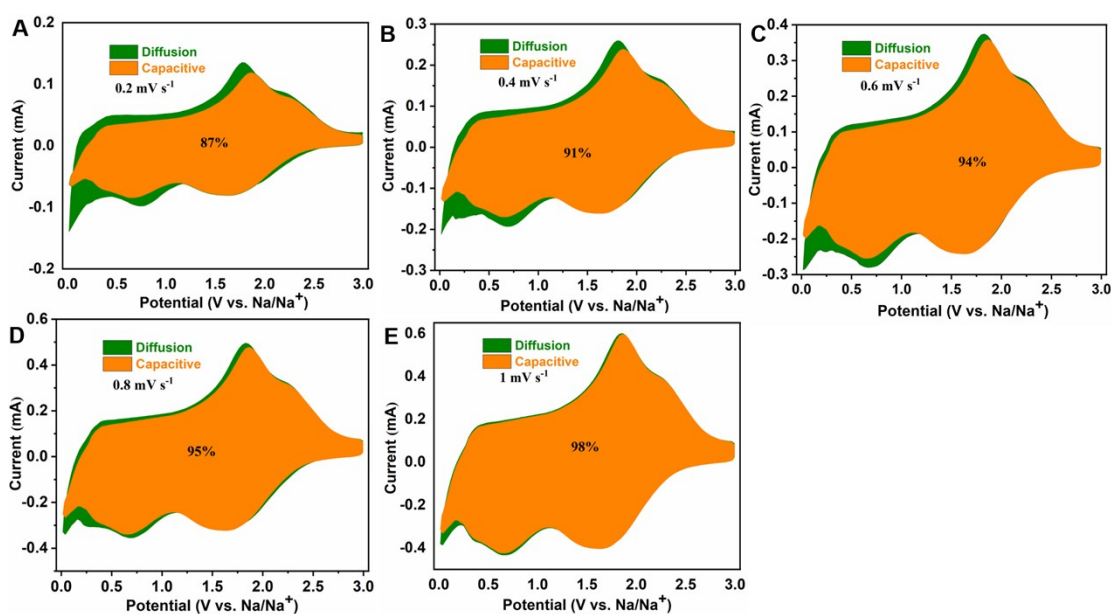


Fig. S4 Capacitive charge storage contribution (orange) and diffusion charge storage contribution (olive) at 0.2 (A) mV s⁻¹, 0.4 (B) mV s⁻¹, 0.6 (C) mV s⁻¹, 0.8 (D) mV s⁻¹ and 1 (E) mV s⁻¹.